



RAN - 1903000203020091

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S. Y. B. Sc. (Electronics) (Sem. - III) Examination

March - 2023

Electronics : Paper - III

Electronics Circuits and Applications

Time: 1 Hour]

[Total Marks: 50

સૂચના : / Instructions

(1)

નીચે દર્શાવેલ નિશાનીવાળી વિગતો ઉત્તરવહી પર અવશ્ય લખવી.
Fill up strictly the details of signs on your answer book

Name of the Examination:

S. Y. B. Sc. (Electronics) (Sem. - III)

Name of the Subject :

Electronics : Paper - III Electronics Circuits and Applications

Subject Code No.: **1903000203020091**

Seat No.:

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Student's Signature

- (2) Symbols used have their usual meaning.
- (3) Each MCQ Q. 1 to Q. 16 carries one mark.
- (4) Each MCQ Q. 17 to Q. 33 carries two marks.

***O.M.R. Sheet ભરવા અંગેની અગત્યની સૂચનાઓ આપેલ
O.M.R. Sheetની પાછળ છાપેલ છે.***

***Important instructions to fillup O.M.R. Sheet
are given on back side of the provided O.M.R. Sheet.***

- Q. 7.** The cause of small voltage gains for an RC coupled amplifier in the high frequency region compared to mid frequency region is due to
- A) Coupling capacitors B) Series capacitor
C) Shunt capacitor D) None
- Q. 8.** In bias compensation technique we can stabilize collector current due to variation in
- A) Temperature only
B) Transistor parameter only
C) Temperature and Transistor parameter
D) None
- Q. 9.** Hybrid equivalent circuit for transistor is a
- A) Small signal model B) Large signal model
C) Both A & B D) None
- Q. 10.** Trans-conductance factor g_m is related to
- A) BJT B) FET
C) UJT D) None
- Q. 11.** For FET input current is generally assumed to be
- A) Zero B) Infinity
C) Negative D) Positive
- Q. 12.** h_{fb} is
- A) A positive number B) A negative number
C) Zero D) None

- Q. 13.** Current gain (A_i) for CB amplifier is
- A) A positive number B) A negative number
C) Zero D) All the above
- Q. 14.** Input resistance for CE amplifier is
- A) Greater than h_{ib} B) Less than h_{ie}
C) Equal to h_{ib} D) Greater than h_{ie}
- Q. 15.** In class B amplifier the Q – point is located
- A) At the centre of the active region
B) Near the saturation region
C) Near the cut off region
D) Below the cut off region
- Q. 16.** CC amplifier is used as
- A) Voltage amplifier B) Current amplifier
C) Power amplifier D) Buffer

SECTION - II

- Q. 17.** Find the value of R_c of voltage divider bias circuit for the following data.
 $I_{cq} = 10 \text{ mA}$, $\beta = 80$, $V_{ceq} = 8 \text{ V}$, $V_{cc} = 20 \text{ V}$.
- A) 10Ω B) $1 \text{ k}\Omega$
C) $10 \text{ k}\Omega$ D) None
- Q. 18.** An emitter bias circuit is configured with $R_B = 430 \text{ k}\Omega$, $R_C = 2.0 \text{ k}\Omega$, $\beta = 50$, $R_E = 1 \text{ k}\Omega$ and $V_{cc} = 20 \text{ V}$. Find its collector emitter voltage.
- A) 13.97 mV B) 1.397 V
C) 13.97 V D) None

Q. 19. The equations relating the input and output voltages and currents in a transistor's hybrid equivalent circuit are given by

A) $V_1 = h_i I_1 + h_r V_2, I_2 = h_f I_1 + h_o V_2$

B) $I_1 = h_i I_1 + h_r V_2, V_2 = h_f I_1 + h_o V_2$

C) $V_1 = h_i I_1 - h_r V_2, I_2 = h_f I_1 - h_o V_2$

D) $V_2 = h_i I_1 + h_r V_2, I_1 = h_f I_1 + h_o V_2$

Q. 20. In class A amplifier the conduction angle is

A) 180°

B) 360°

C) 270°

D) 0°

Q. 21. Using approximate hybrid model calculate the input resistance of common emitter amplifier with bypassed R_e . $h_{fe} = 280, h_{ie} = 1 \text{ k}\Omega$ and $h_{re} = 0.00015$.

A) 1Ω

B) $10 \text{ k}\Omega$

C) $1 \text{ k}\Omega$

D) $1 \text{ M}\Omega$

Q. 22. Find the value of R_E of voltage divider bias circuit for the following data.

$I_{cq} = 10 \text{ mA}, \beta = 80, V_{ceq} = 8 \text{ V}, V_{cc} = 20 \text{ V}.$

A) 200Ω

B) $2 \text{ k}\Omega$

C) $10 \text{ k}\Omega$

D) None

Q. 23. Which condition must be satisfied for a voltage divider biasing circuit so that it becomes independent of β ?

A) $R_E = R_2$

B) $R_E = 10R_2$

C) $\beta R_E = 10R_2$

D) $\beta R_2 = 10R_E$

Q. 24. A voltage divider bias circuit is configured with $R_1 = 82 \text{ k}\Omega, R_2 = 22 \text{ k}\Omega, R_C = 5.6 \text{ k}\Omega, \beta = 50, R_E = 1.2 \text{ k}\Omega$ and $V_{cc} = 18 \text{ V}$. What is its collector emitter voltage?

A) 4.54 V

B) 4.54 mV

C) 5.45 V

D) None

Q. 25. Shockley's equation is

- A) $I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2$ B) $I_D = I_{DSS} \left(1 + \frac{V_{GS}}{V_P}\right)^2$
C) $I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)$ D) None

Q. 26. The device parameters for N channel FET are :

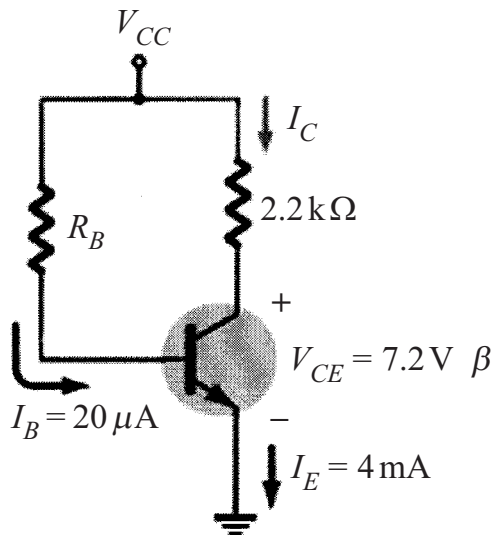
Maximum drain current (I_{DSS}) = 10 mA, pinch-off voltage $V_p = -4V$. calculate the drain current for $V_{GS} = 0V$.

- A) 0 mA B) 10 mA
C) 10 A D) 10 A

Q. 27. A silicon transistor is used for making an amplifier using voltage divider bias circuit with emitter bias having a power supply of 20V, $R_1 = 22 k\Omega$ and $R_2 = 5 k\Omega$, then what will be the value of voltage at the emitter terminal?

- A) 20 V B) 3 V
C) 0.7 V D) 0.3 V

Q. 28. In the figure given below Find out β .



- A) 199 B) 398
C) 19.9 D) None

SPACE FOR ROUGH WORK